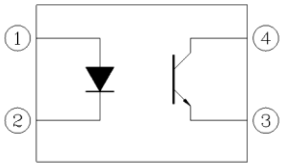
4 PIN SOP PHOTOTRANSISTOR PHOTOCOUPLER
EL357N-G Series

Schematic



Pin Configuration
1. Anode
2. Cathode
3. Emitter
4. Collector

Features:

- Halogens free
  (Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm)
- Current transfer ratio
  (CTR: 50~600% at I_F =5mA, V_{CE} =5V)
- High isolation voltage between input and output (Viso=3750 V rms)
- Compact 4 Pin SOP with a 2.0 mm profile
- Compliance with EU REACH
- Pb free and RoHS compliant
- UL and cUL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved

Description

The EL357N-G series contains an infrared emitting diode, optically coupled to a phototransistor detector.

The devices in a 4-pin small outline SMD package.

Applications

- DC-DC Converters
- Programmable controllers
- Telecommunication equipments
- Signal transmission between circuits of different potentials and impedances

Absolute Maximum Ratings (Ta=25℃)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	Peak forward current (1us, pulse)	I_{FP}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P_D	70	mW
	Derating factor (about Ta=100°C)		2.9	mW/C
Output	Power dissipation	P_C	150	mW
	Derating factor (above T_a = 70°C)		3.7	mW/°C
	Collector current	I_C	50	mA
	Collector-Emitter voltage	V_{CEO}	80	V
	Emitter-Collector voltage	V_{ECO}	7	V
Total Power Dissipation		P_{TOT}	200	mW
Isolation Voltage*1		V_{ISO}	3750	V rms
Operating temperature		T_{OPR}	-55 ~ +110	°C
Storage temperature		T_{STG}	-55 ~ +125	°C
Soldering Temperature*2		T_{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 are shorted together, and pins 3, 4 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (Ta=25℃ unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward voltage	V_F	-	1.2	1.4	V	I_F = 20mA
Reverse current	I_R	-	-	10	μA	V_R = 4V
Input capacitance	C_{in}	-	30	250	pF	V = 0, f = 1kHz

Output

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	V_{CE} = 20V, I_F = 0mA
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	I_C = 0.1mA
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	I_E = 0.01mA

Transfer Characteristics (T_a=25°C unless specified otherwise)

Parameter		Symbol	Min	Typ.	Max.	Unit	Condition
Current Transfer ratio	EL357N	CTR	50	-	600	%	I_F = 5mA ,V_{CE} = 5V
	EL357NA		80	-	160		
	EL357NB		130	-	260		
	EL357NC		200	-	400		
	EL357ND		300	-	600		
	EL357NE		100	-	200		
	EL357NF		150	-	300		
Collector-Emitter saturation voltage		$V_{CE(sat)}$	-	0.1	0.2	V	I_F = 20mA ,I_C = 1mA
Isolation resistance		R_{IO}	5×10^{10}	-	-	Ω	V_{IO} = 500Vdc, 40~60% R.H.
Floating capacitance		C_{IO}	-	0.6	1.0	pF	V_{IO} = 0, f = 1MHz
Rise time		t_r	-	3	18	μs	V_{CE} = 2V, I_C = 2mA, R_L = 100Ω
Fall time		t_f	-	4	18		

* Typical values at T_a = 25°C

Typical Electro-Optical Characteristics Curves

Figure 1. Forward Current vs Forward Voltage

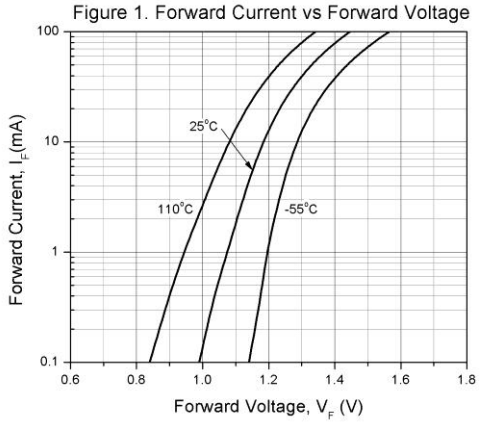


Figure 2. Normalized Collector Current vs Forward Current

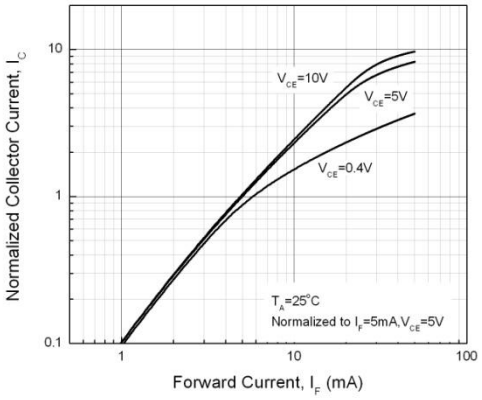


Figure 3. Normalized Current Transfer Ratio vs Forward Current

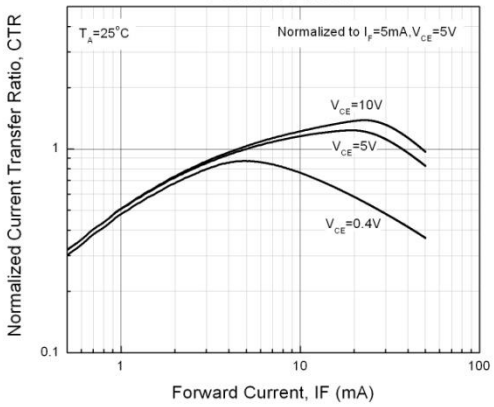


Figure 4. Normalized Collector Current vs Ambient Temperature

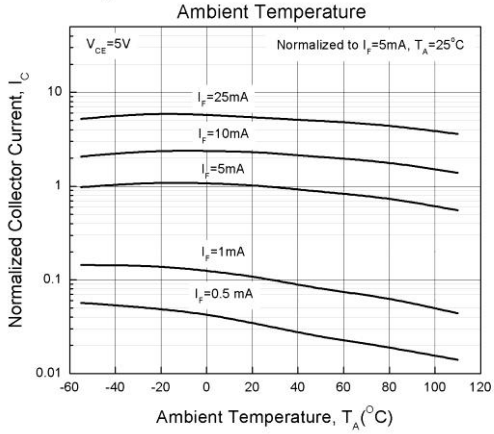


Figure 5. Collector Current vs Collector-Emitter Voltage

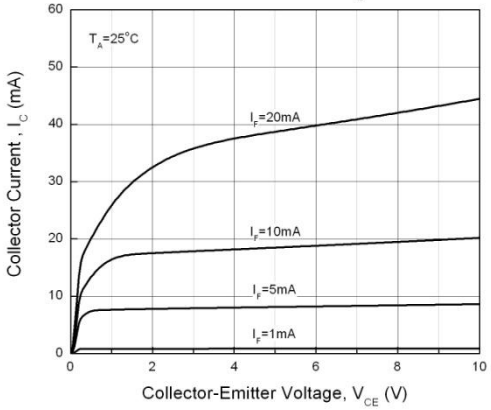


Figure 6. Collector Current vs Collector-Emitter Voltage